

N-channel 80 V, 17 mΩ standard level MOSFET in LFPAK33 19 September 2016 Product data sheet

### 1. General description

Standard level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)}$  rating of greater than 1 V at 175 °C

### 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

| Table 1. Qui      | ck reference data                |   |     |     |     |      |
|-------------------|----------------------------------|---|-----|-----|-----|------|
| Symbol            | Parameter                        | Conditions  | Min | Тур | Max | Unit |
| V <sub>DS</sub>   | drain-source voltage             | 25 °C ≤ T <sub>j</sub> ≤ 175 °C   | -   | -   | 80  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>                              | -   | -   | 43  | А    |
| P <sub>tot</sub>  | total power dissipation          | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>  | -   | -   | 79  | W    |
| Static charact    | eristics                         |   |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C;<br>Fig. 11           | -   | 14  | 17  | mΩ   |
| Dynamic char      | acteristics                      |   |     |     |     |      |
| Q <sub>GD</sub>   | gate-drain charge                | $I_D$ = 10 A; $V_{DS}$ = 64 V; $V_{GS}$ = 10 V;<br>T <sub>j</sub> = 25 °C; Fig. 13; Fig. 14 | -   | 9.7 | -   | nC   |

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### 5. Pinning information

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | S       | Source                            |                    | D              |
| 2        | S       | Source                            |                    |                |
| 3        | S       | Source                            | $\bigcirc$         | G              |
| 4        | G       | Gate                              |                    | mbb076 S       |
| mb       | D       | Mounting base; connected to drain | LFPAK33 (SOT1210)  |                |

# 6. Ordering information

| Fable 3. Ordering information |         |   |         |  |  |  |
|-------------------------------|---------|---|---------|--|--|--|
| Type number                   | Package | age   |         |  |  |  |
|                               | Name    | Description   | Version |  |  |  |
| BUK7M17-80E                   | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 8 leads | SOT1210 |  |  |  |

# 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BUK7M17-80E            | 71780E       |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   | Min | Max | Unit |
|------------------|-------------------------|--|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                  | -   | 80  | V    |
| V <sub>DGR</sub> | drain-gate voltage      | R <sub>GS</sub> = 20 kΩ  | -   | 80  | V    |
| V <sub>GS</sub>  | gate-source voltage     | DC; T <sub>j</sub> ≤ 175 °C                                      | -20 | 20  | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                           | -   | 79  | W    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>   | -   | 43  | А    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>  | -   | 30  | А    |
| I <sub>DM</sub>  | peak drain current      | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3 | -   | 173 | А    |
| T <sub>stg</sub> | storage temperature     |  | -55 | 175 | °C   |

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| Symbol               | Parameter                                    | Conditions   |        | Min | Мах  | Unit |
|----------------------|--|--|--------|-----|------|------|
| Tj                   | junction temperature                         |  |        | -55 | 175  | °C   |
| Source-dra           | in diode                                     |  | 1      |     |      |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C  |        | -   | 43   | А    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$  |        | -   | 173  | А    |
| Avalanche            | ruggedness                                   |  |        |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $    I_D = 43 \text{ A}; V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 4 $ | [1][2] | -   | 47.4 | mJ   |

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^\circ$ C.

[2] Refer to application note AN10273 for further information.

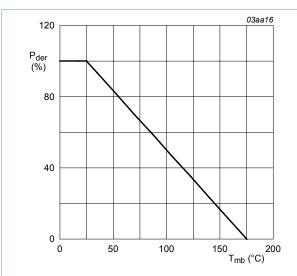
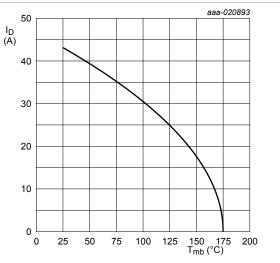


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

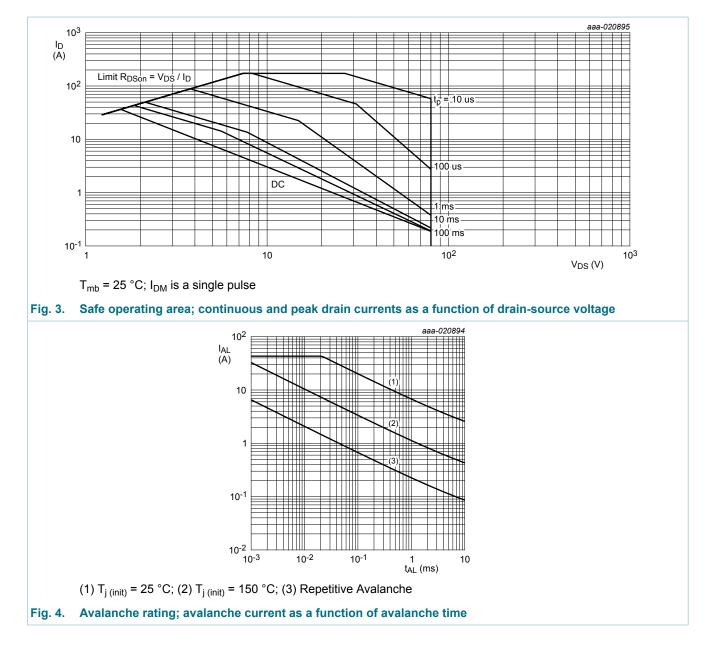


V<sub>GS</sub> ≥ 10 V

Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 43A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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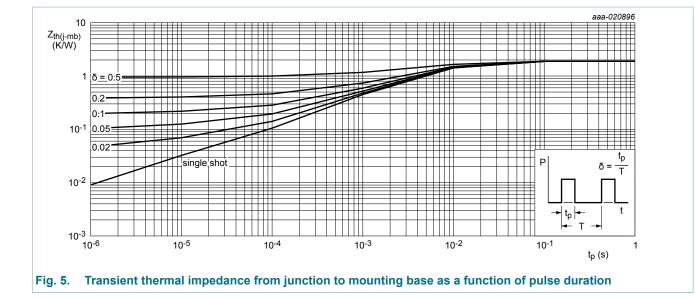


### 9. Thermal characteristics

| Table 6. The          | ermal characteristics                                   |            |     |      |      |      |
|-----------------------|---|------------|-----|------|------|------|
| Symbol                | Parameter   | Conditions | Min | Тур  | Max  | Unit |
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5     | -   | 1.58 | 1.89 | K/W  |

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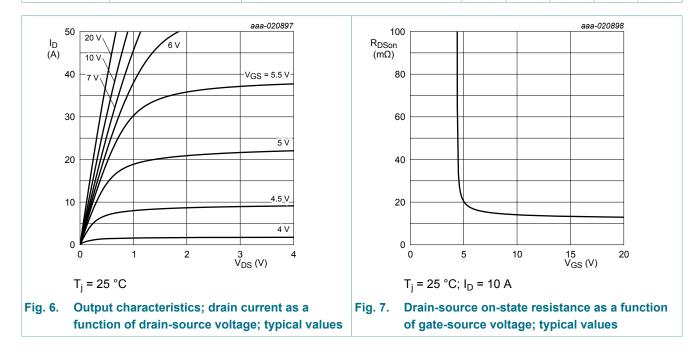
### **10. Characteristics**

| Symbol  | Parameter  | Conditions   | Min | Тур  | Max | Unit |
|---|--|--|-----|------|-----|------|
| Static chara                                      | acteristics  | · · · ·  | I   |      |     |      |
| V <sub>(BR)DSS</sub>                              | drain-source   | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                      | 80  | -    | -   | V    |
|   | breakdown voltage  | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C                                     | 72  | -    | -   | V    |
| V <sub>GS(th)</sub> gate-source threshold voltage | gate-source threshold voltage  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C;<br>Fig. 9; Fig. 10              | 2.4 | 3    | 4   | V    |
|   | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$<br>Fig. 9 | ,  | -   | -    | 4.5 | V    |
|   |  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$<br>Fig. 9             | 1   | -    | -   | V    |
| I <sub>DSS</sub>                                  | DSS drain leakage current  | $V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                     | -   | 0.01 | 1   | μA   |
|   |  | $V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C                                    | -   | -    | 500 | μA   |
| I <sub>GSS</sub>                                  | GSS gate leakage current   | $V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                     | -   | 2    | 100 | nA   |
|   |  | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                                    | -   | 2    | 100 | nA   |
| R <sub>DSon</sub>                                 | drain-source on-state resistance                                       | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C;<br>Fig. 11  | -   | 14   | 17  | mΩ   |
|   |  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C;<br>Fig. 12 | -   | -    | 43  | mΩ   |
| Dynamic ch  | naracteristics   | · · · ·  |     |      |     |      |
| Q <sub>G(tot)</sub>                               | total gate charge  | $I_D$ = 10 A; $V_{DS}$ = 64 V; $V_{GS}$ = 10 V;                                    | -   | 29.6 | -   | nC   |
| Q <sub>GS</sub>                                   | gate-source charge   | T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>                                    | -   | 6.5  | -   | nC   |
| Q <sub>GD</sub>                                   | gate-drain charge  |  | -   | 9.7  | -   | nC   |

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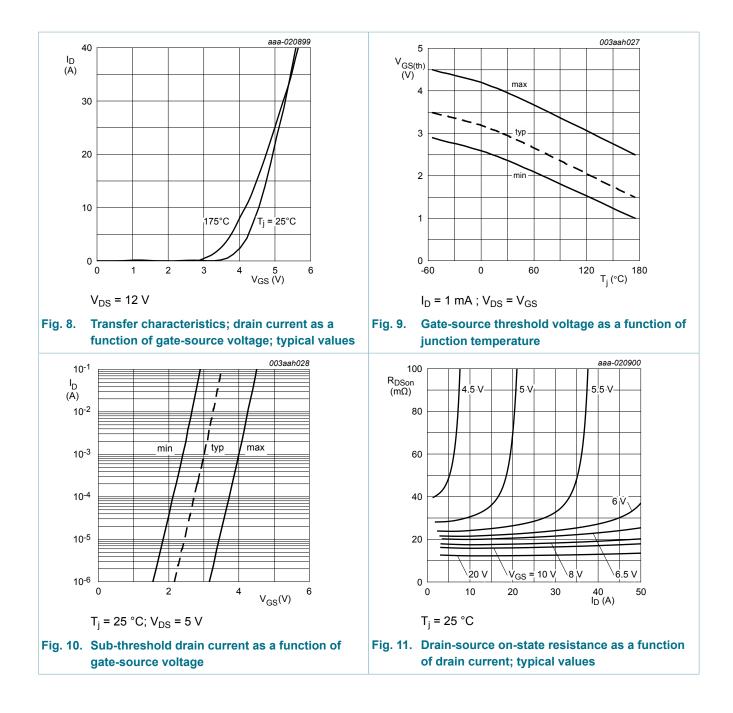
#### N-channel 80 V, 17 m $\Omega$ standard level MOSFET in LFPAK33

| Symbol              | Parameter                    | Conditions  | Min | Тур  | Мах  | Unit |
|---------------------|------------------------------|---|-----|------|------|------|
| C <sub>iss</sub>    | input capacitance            | $V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;                             | -   | 1527 | 2031 | pF   |
| C <sub>oss</sub>    | output capacitance           | T <sub>j</sub> = 25 °C; <u>Fig. 15</u>                                  | -   | 161  | 193  | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance |   | -   | 97   | 133  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | $V_{DS}$ = 60 V; R <sub>L</sub> = 5 Ω; V <sub>GS</sub> = 10 V;          | -   | 6.7  | -    | ns   |
| t <sub>r</sub>      | rise time                    | R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C                       | -   | 9.4  | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |   | -   | 22.3 | -    | ns   |
| t <sub>f</sub>      | fall time                    |   | -   | 12   | -    | ns   |
| Source-dra          | ain diode                    | 1   | 1   |      |      |      |
| V <sub>SD</sub>     | source-drain voltage         | $I_{S}$ = 10 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>         | -   | 0.81 | 1.2  | V    |
| t <sub>rr</sub>     | reverse recovery time        | $I_{S}$ = 10 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; | -   | 26   | -    | ns   |
| Q <sub>r</sub>      | recovered charge             | V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C                          | -   | 33.9 | -    | nC   |



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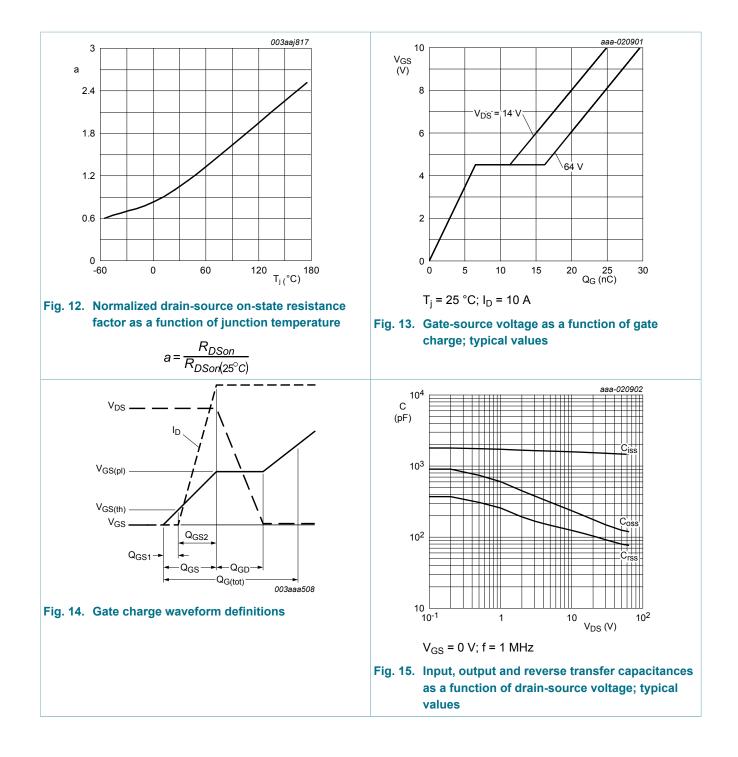
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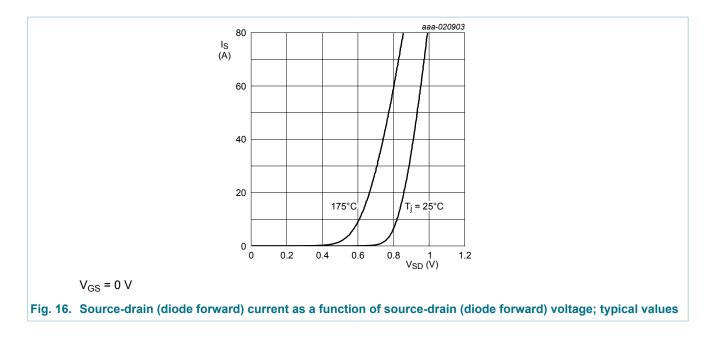
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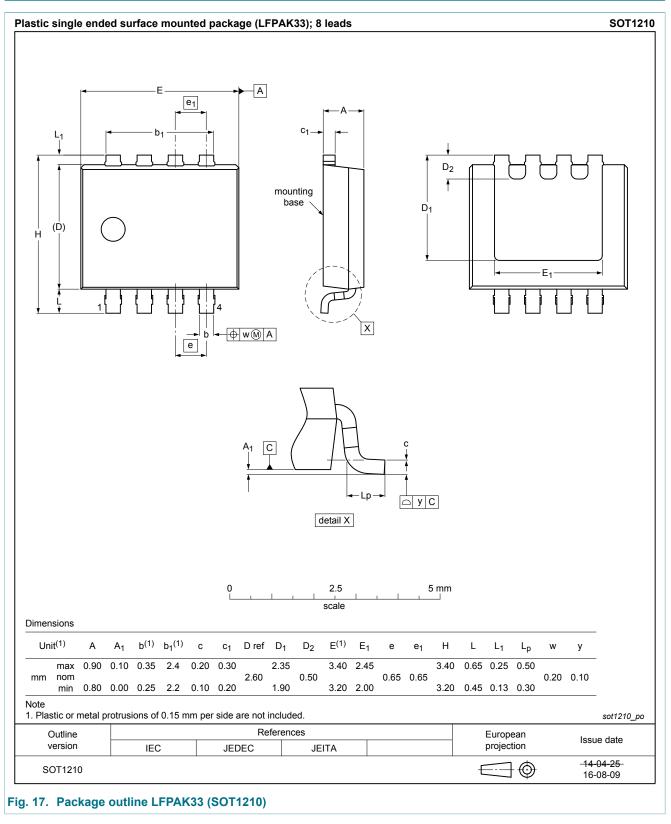


# **11. Application information**

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

N-channel 80 V, 17 mΩ standard level MOSFET in LFPAK33

### 12. Package outline



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#### N-channel 80 V, 17 mΩ standard level MOSFET in LFPAK33

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|--------------------------------------|-------------------------------|---|
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